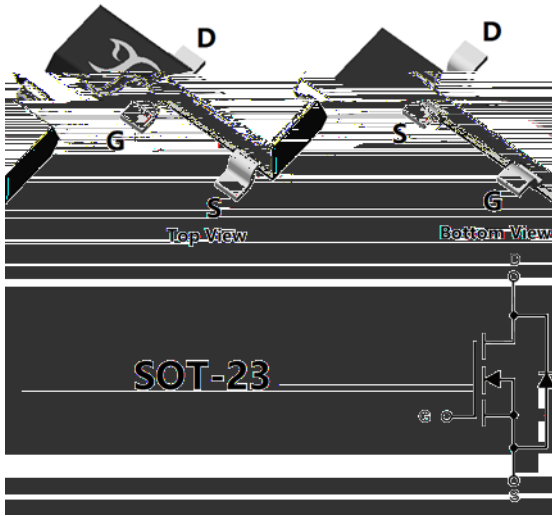




## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

$V_{DS}$	40V
$I_D$	5A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	33m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	50m

### General Description

Trench Power MV MOSFET technology  
 High Speed switching  
 Moisture Sensitivity Level 1  
 Epoxy Meets UL 94 V-0 Flammability Rating  
 Halogen Free

### Applications

Power switching application  
 Uninterruptible power supply  
 Load switch

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	40	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_A=25$	5
		$T_A=100$	3
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	30	A
Total Power Dissipation <sup>B</sup>	$P_D$	$T_A=25$	1.2
		$T_A=100$	0.5
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 +150	

### Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>C</sup>	$R_{JA}$	80	100	$^{\circ}W$

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL05N04C	F2	05N04C.	3000	30000	120000	7" reel



# YJL05N04C

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
		$V_{DS}=40V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	-	25	33	m
		$V_{GS}=4.5V, I_D=3A$	-	38	50	
Diode Forward Voltage	$V_{SD}$	$I_S=5A, V_{GS}=0V$	-	0.9	1.2	V
Gate resistance	$R_G$	$f=1MHz$	-	2.2	-	
Maximum Body-Diode Continuous Current	$I_S$		-	-	5	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V, f=1MHz$	-	390	-	$\mu F$
Output Capacitance	$C_{oss}$		-	50	-	
Reverse Transfer Capacitance	$C_{rss}$		-	40	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=20V, I_D=5A$	-	11	-	nC
Gate-Source Charge	$Q_{gs}$		-	3	-	
Gate-Drain Charge	$Q_{gd}$		-	3	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=5A, di/dt=100A/us$	-	19	-	nC
Reverse Recovery Time	$t_{rr}$		-	26	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=20V, I_D=5A$ $R_{GEN}=2.2$	-	6	-	ns
Turn-on Rise Time	$t_r$		-	20	-	
Turn-off Delay Time	$t_{D(off)}$		-	12	-	
Turn-off fall Time	$t_f$		-	2	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $P_g$  is based on max. junction temperature, using junction-case thermal resistance.

C. The value of  $R_{JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25$ . The maximum allowed junction temperature of 150. The value in any given application depends on the user's specific board design.



## Typical Electrical and Thermal Characteristics Diagrams

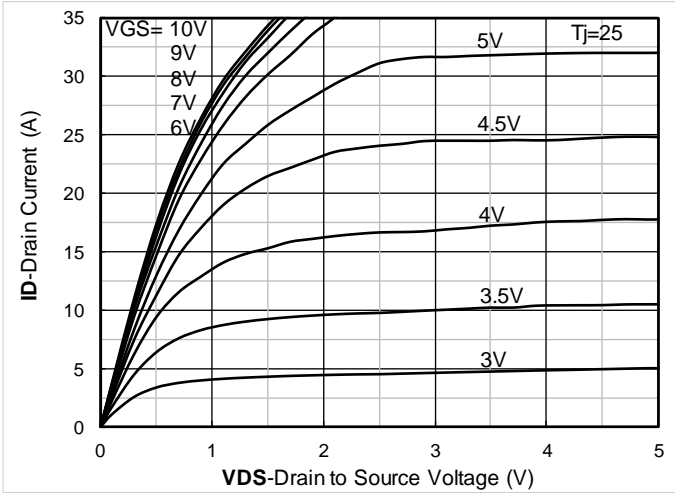


Figure 1. Output Characteristics

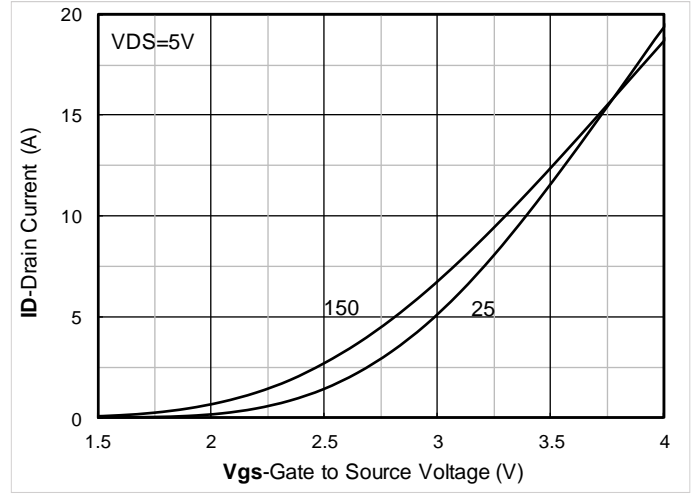


Figure 2. Transfer Characteristics

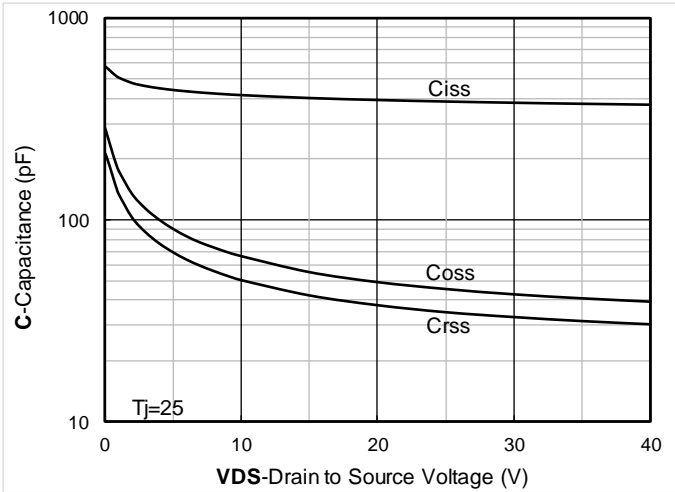


Figure 3. Capacitance Characteristics

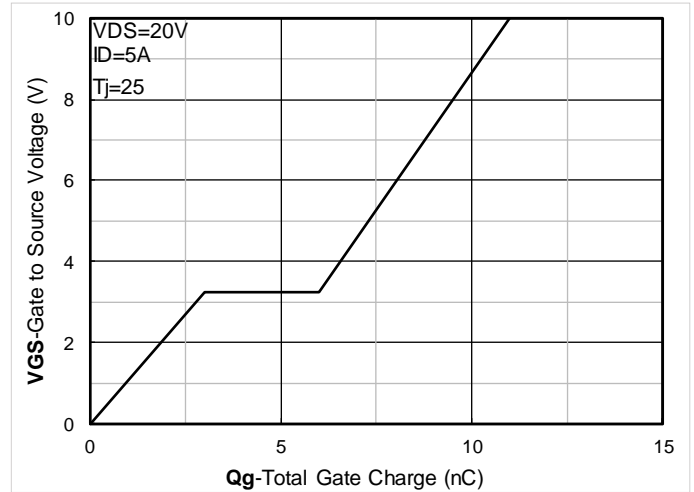


Figure 4. Gate Charge

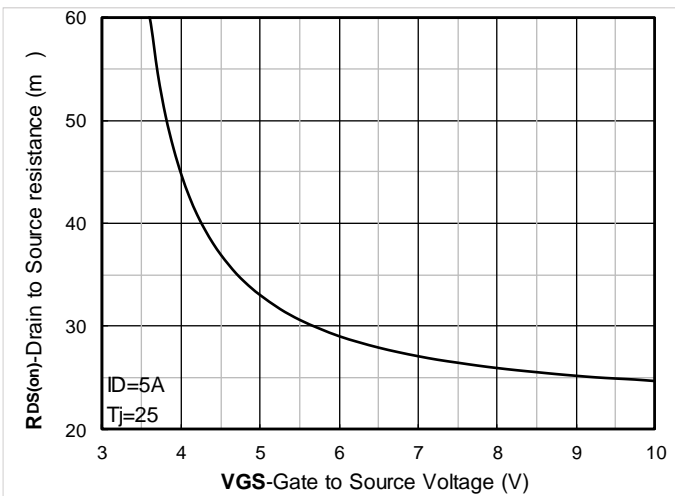


Figure 5. On-Resistance vs Gate to Source Voltage

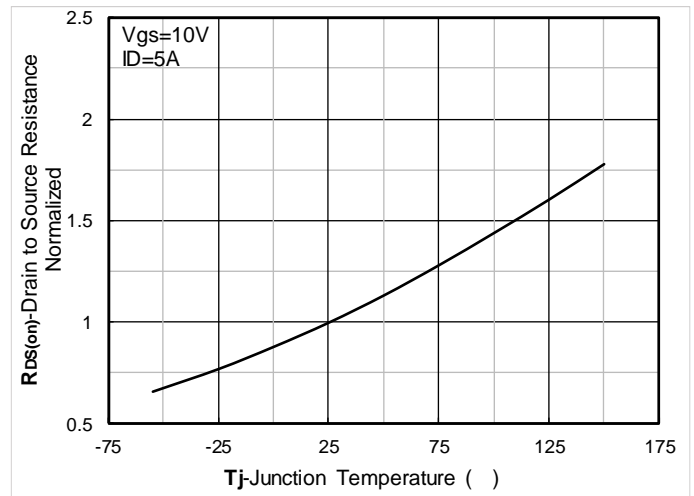


Figure 6. Normalized On-Resistance



# YJL05N04C

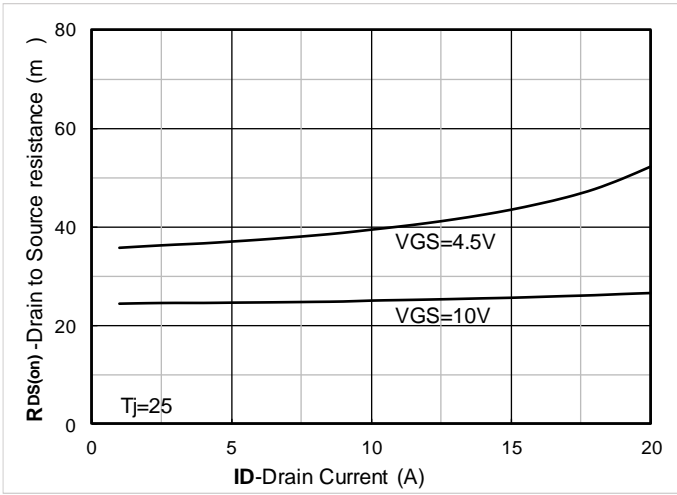


Figure 7.  $R_{DS(on)}$  VS Drain Current

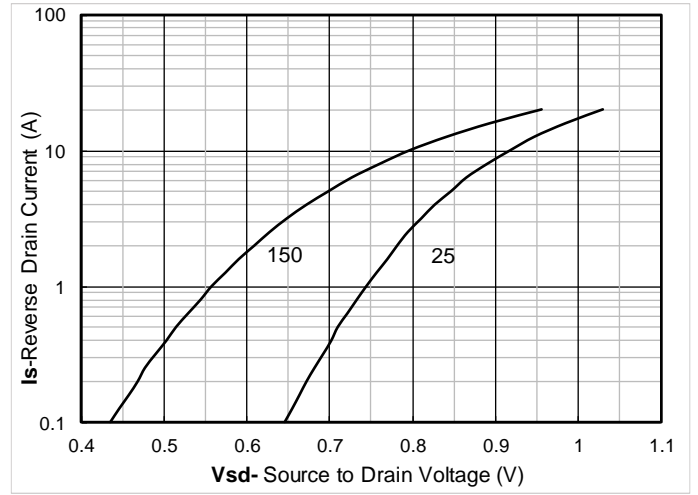


Figure 8. Forward characteristics of reverse diode

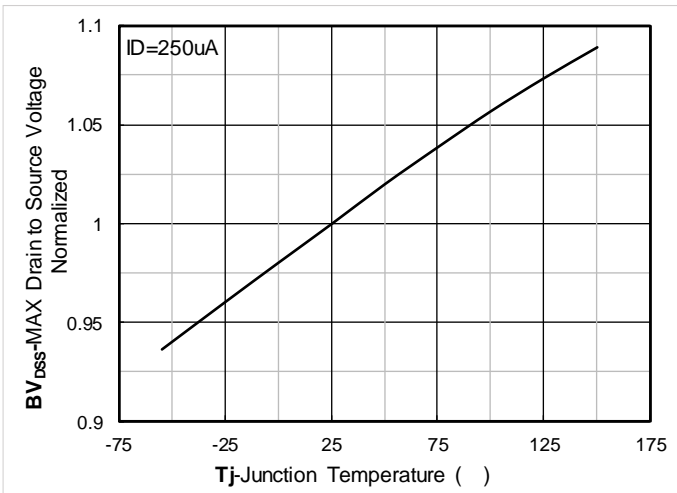


Figure 9. Normalized breakdown voltage

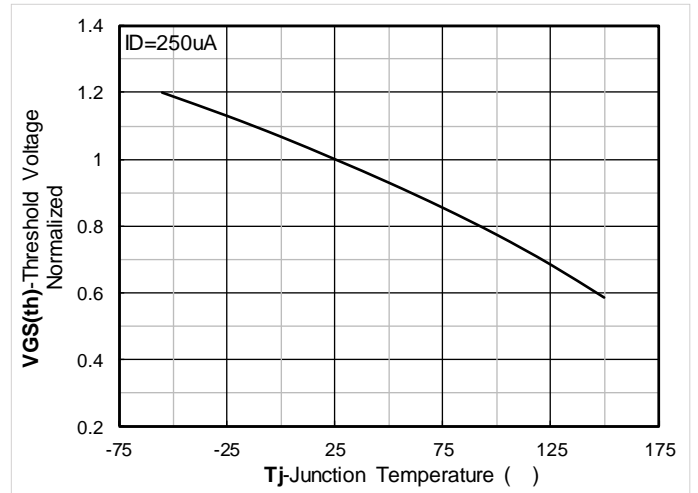


Figure 10. Normalized Threshold voltage

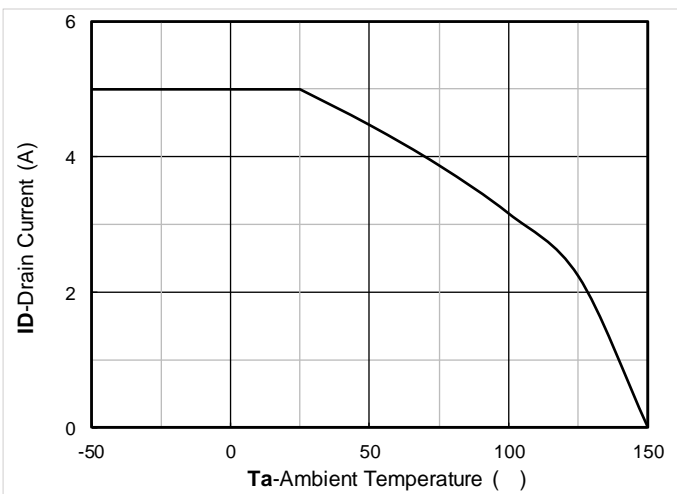


Figure 11. Current dissipation

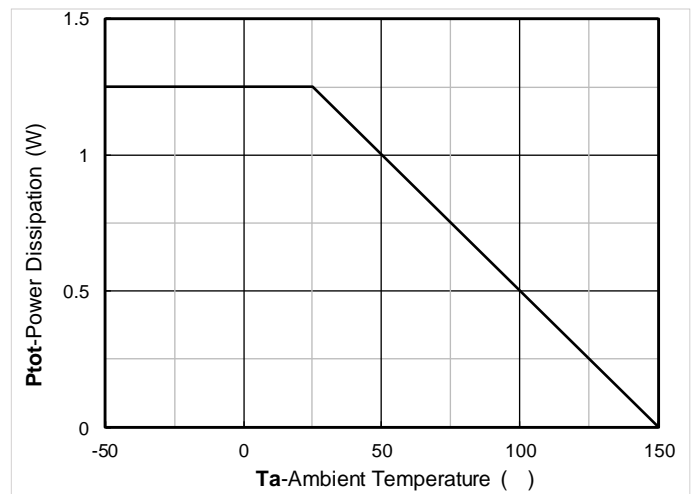


Figure 12. Power dissipation



Figure 13. Maximum Transient Thermal Impedance

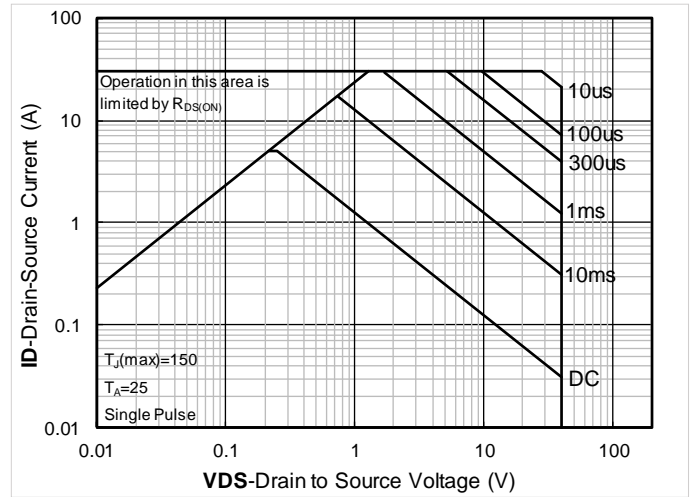


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

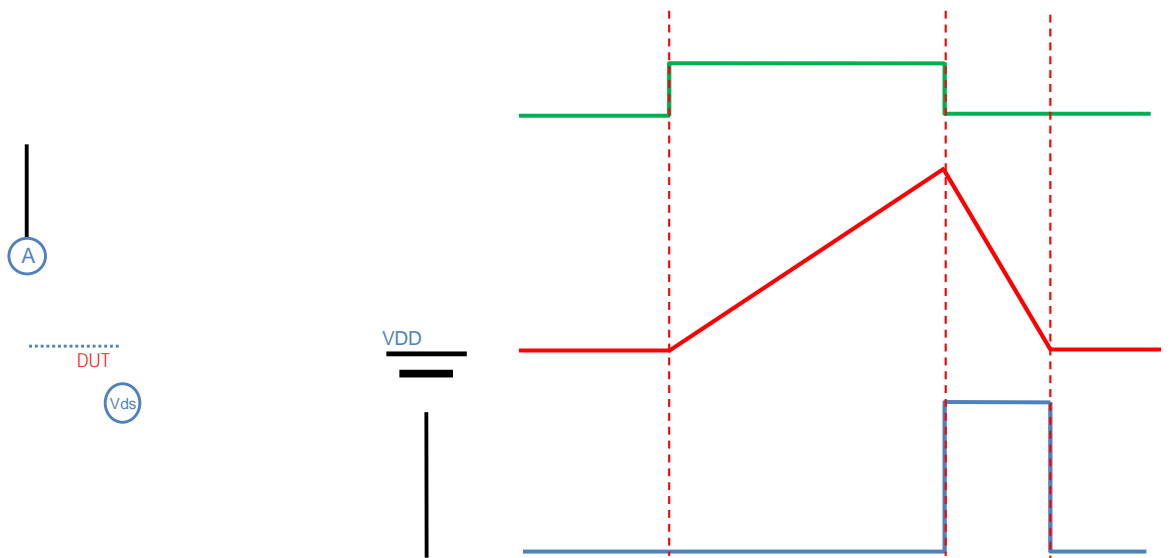


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

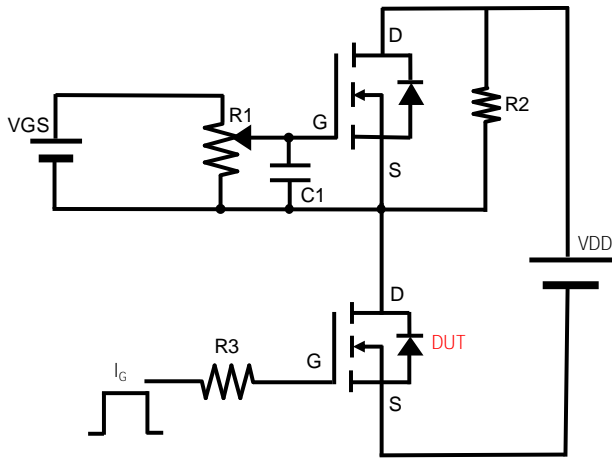


Figure B. Gate Charge Test Circuit & Waveform

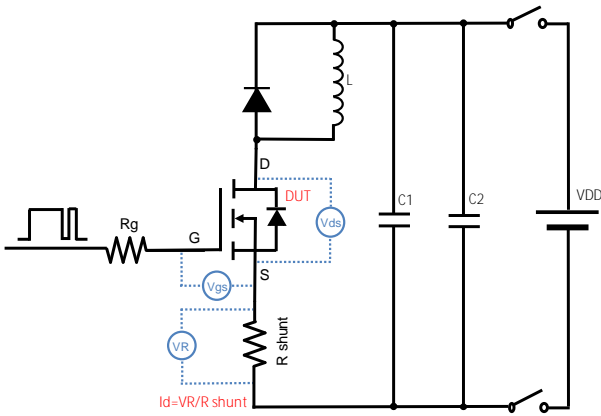


Figure C. Resistive Switching Test Circuit & Waveform

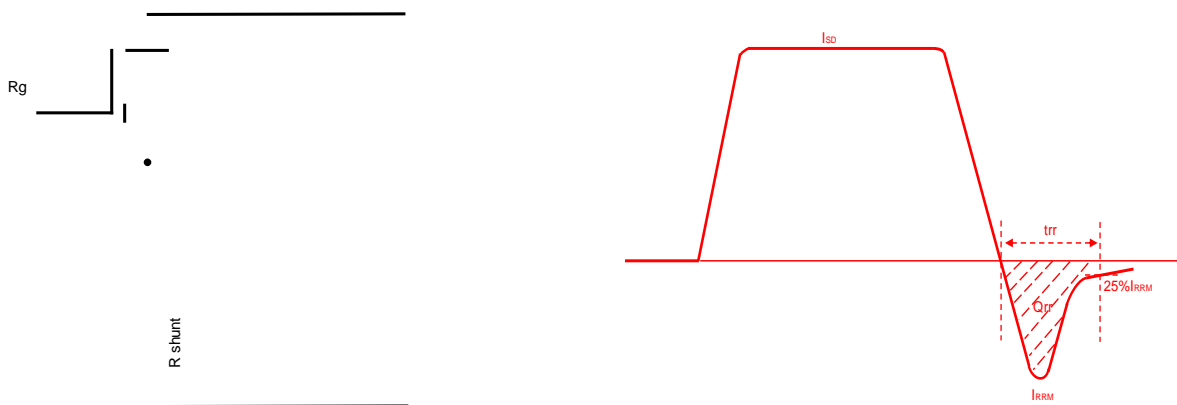
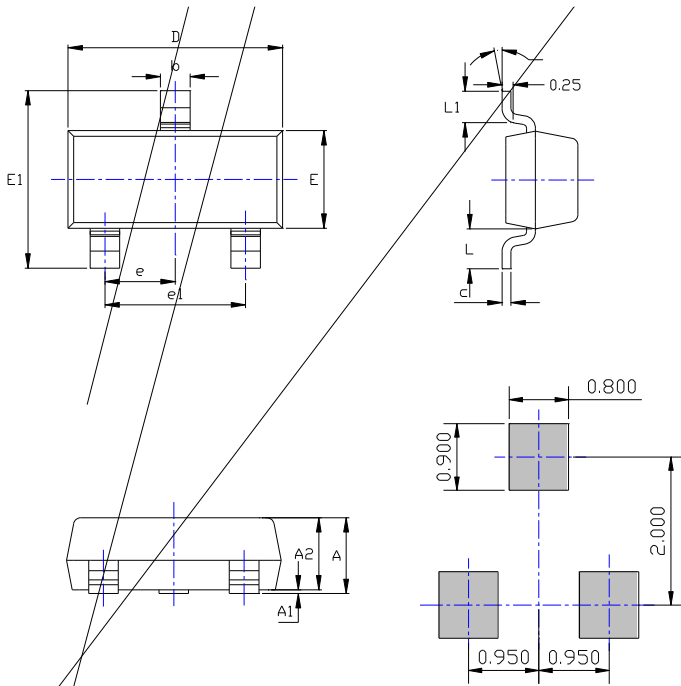


Figure D. Diode Recovery Test Circuit & Waveform



# YJL05N04C

## SOT-23 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	(			

UNIT mm



## YJL05N04C

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